



Fast Recovery Diodes (Hockey PUK Version), 700/790 A



DO-200AB (B-PUK)

FEATURES

- High power fast recovery diode series
- 2.0 μ s to 3.0 μ s recovery time
- High voltage ratings up to 2500 V
- High current capability
- Optimized turn-on and turn-off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® DO-200AB (B-PUK)
- Maximum junction temperature 150 °C
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY	
$I_{F(AV)}$	700/790 A
Package	DO-200AB (B-PUK)
Circuit configuration	Single diode

TYPICAL APPLICATIONS

- Snubber diode for GTO
- High voltage freewheeling diode
- Fast recovery rectifier applications

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	SD703C..L		UNITS
		S20	S30	
$I_{F(AV)}$		700	790	A
	T_{hs}	55	55	°C
$I_{F(RMS)}$		1320	1470	A
I_{FSM}	50 Hz	9300	9600	
	60 Hz	9730	10 050	
V_{RRM}	Range	1200 to 2500	1200 to 2500	V
t_{rr}		2.0	3.0	μ s
	T_J	25	25	°C
T_J		-40 to 150	-40 to 150	

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD703C..L	12	1200	1300	50
	16	1600	1700	
	20	2000	2100	
	25	2500	2600	



FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		SD703C..L		UNITS
				s20	s30	
Maximum average forward current at heatsink temperature	$I_{F(AV)}$	180° conduction, half sine wave Double side (single side) cooled		700 (365)	790 (400)	A
				55 (85)	55 (85)	°C
Maximum RMS forward current	$I_{F(RMS)}$	25 °C heatsink temperature double side cooled		1320	1470	
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms t = 8.3 ms	No voltage reapplied	9300	9600	A
			100 % V_{RRM} reapplied	9730	10 050	
		Sinusoidal half wave, initial $T_J = T_J$ maximum		t = 10 ms t = 8.3 ms	7820	
			8190	8450		
Maximum I^2t for fusing	I^2t	t = 10 ms t = 8.3 ms	No voltage reapplied	432	460	kA ² s
			100 % V_{RRM} reapplied	395	420	
		Sinusoidal half wave, initial $T_J = T_J$ maximum		t = 10 ms t = 8.3 ms	306	
			279	297		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		4320	4600	kA ² √s
Low level value of threshold voltage	$V_{F(TO)1}$	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		1.00	0.95	V
High level value of threshold voltage	$V_{F(TO)2}$	(I $> \pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		1.11	1.05	
Low level value of forward slope resistance	r_{f1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum)		0.80	0.60	mW
High level value of forward slope resistance	r_{f2}	(I $> \pi \times I_{T(AV)}$, $T_J = T_J$ maximum)		0.76	0.56	
Maximum forward voltage drop	V_{FM}	$I_{pk} = 1500$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sinusoidal wave		2.20	1.85	V

RECOVERY CHARACTERISTICS								
CODE	MAXIMUM VALUE AT $T_J = 25$ °C	TEST CONDITIONS			TYPICAL VALUES AT $T_J = 150$ °C			
	t_{rr} AT 25 % I_{RRM} (μs)	I_{pk} SQUARE PULSE (A)	di/dt (A/μs)	V_r (V)	t_{rr} AT 25 % I_{RRM} (μs)	Q_{rr} (μC)	I_{rr} (A)	
S20	2.0	1000	50	- 50	3.5	240	110	
S30	3.0				5.0	380	130	

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction operating and storage temperature range	T_J, T_{Stg}		- 40 to 150	°C	
Maximum thermal resistance, case junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.092	K/W	
		DC operation double side cooled	0.046		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			250	g	
Case style		See dimensions - link at the end of datasheet	DO-200AB (B-PUK)		

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.011	0.011	0.008	0.008	$T_J = T_J$ maximum	K/W
120°	0.013	0.014	0.013	0.013		
90°	0.017	0.017	0.018	0.018		
60°	0.024	0.025	0.026	0.026		
30°	0.043	0.043	0.043	0.044		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

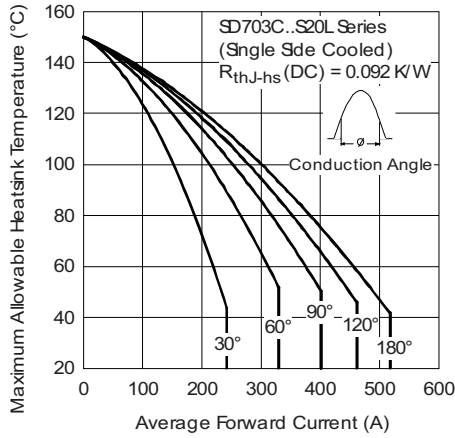


Fig. 1 - Current Ratings Characteristics

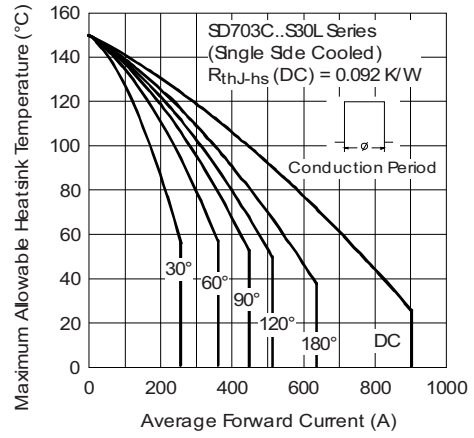


Fig. 4 - Current Ratings Characteristics

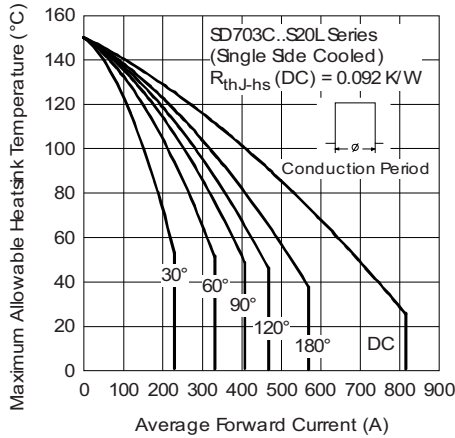


Fig. 2 - Current Ratings Characteristics

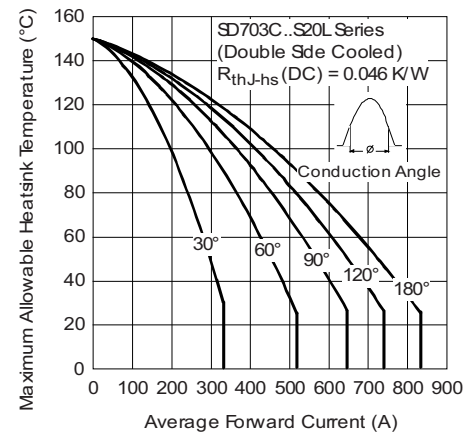


Fig. 5 - Current Ratings Characteristics

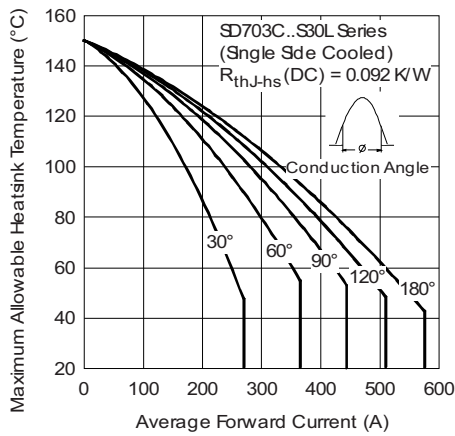


Fig. 3 - Current Ratings Characteristics

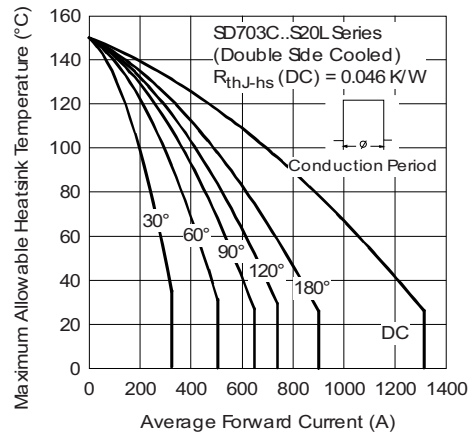


Fig. 6 - Current Ratings Characteristics

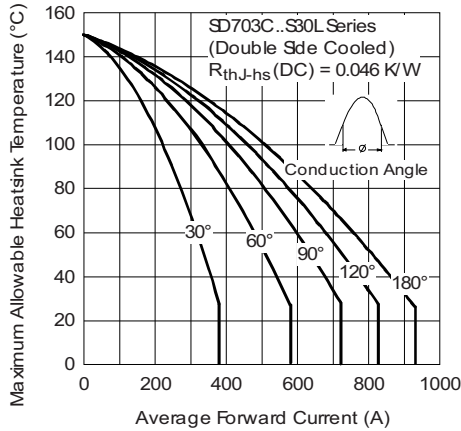


Fig. 7 - Current Ratings Characteristics

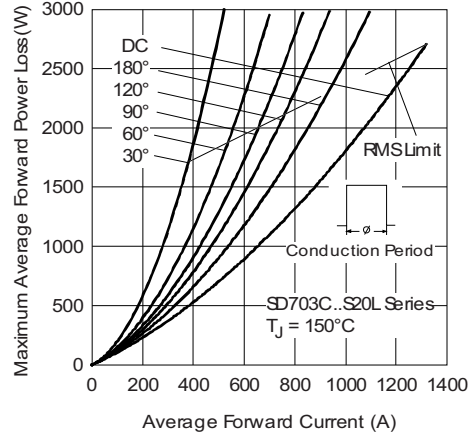


Fig. 10 - Forward Power Loss Characteristics

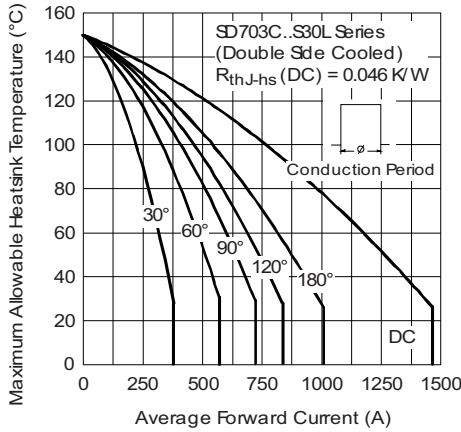


Fig. 8 - Current Ratings Characteristics

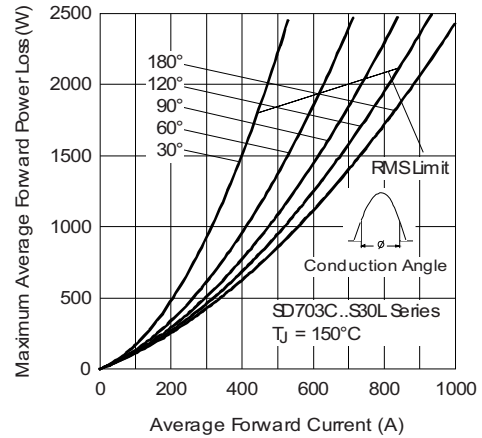


Fig. 11 - Forward Power Loss Characteristics

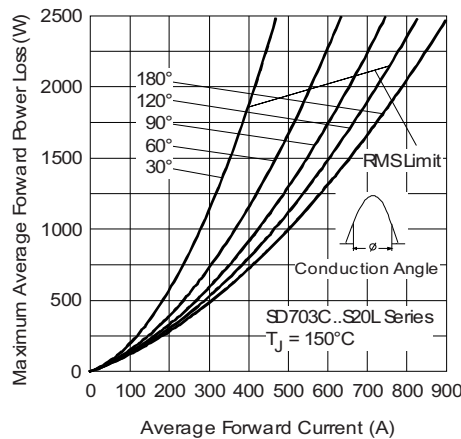


Fig. 9 - Forward Power Loss Characteristics

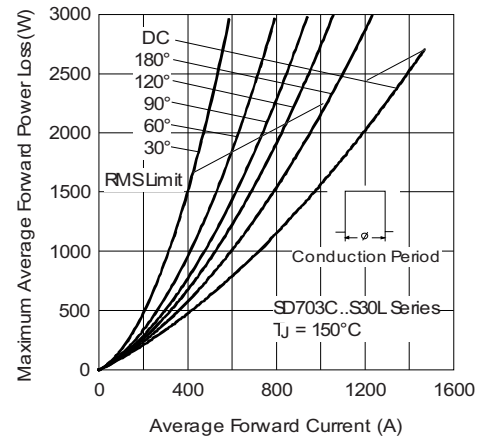


Fig. 12 - Forward Power Loss Characteristics

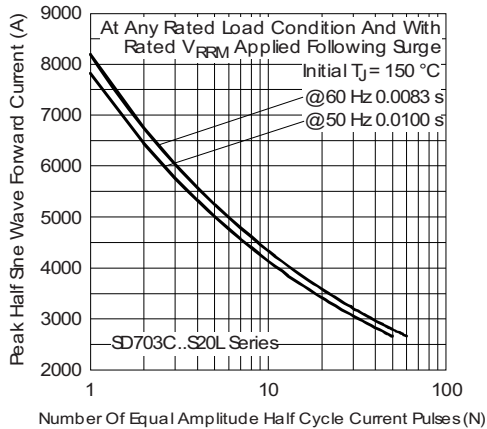


Fig. 13 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

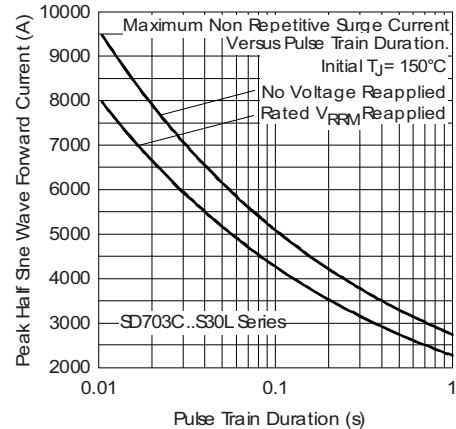


Fig. 16 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

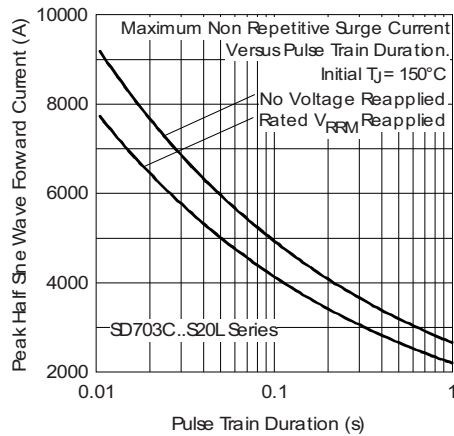


Fig. 14 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

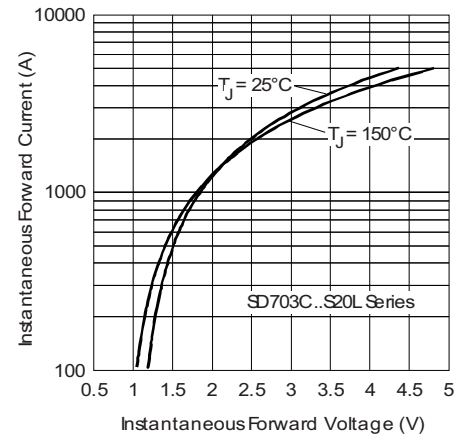


Fig. 17 - Forward Voltage Drop Characteristics

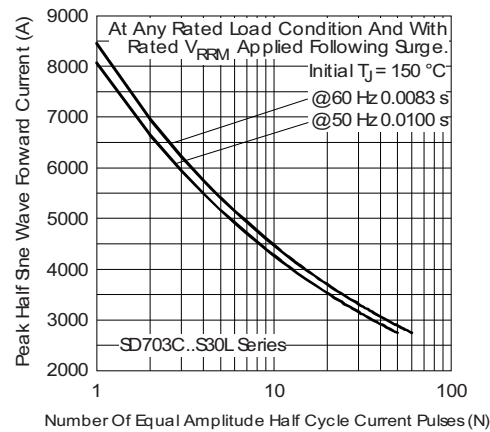


Fig. 15 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

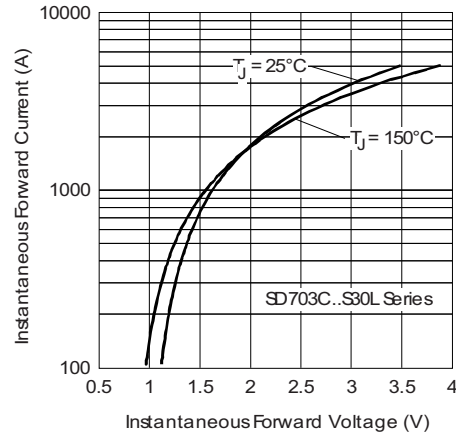


Fig. 18 - Forward Voltage Drop Characteristics

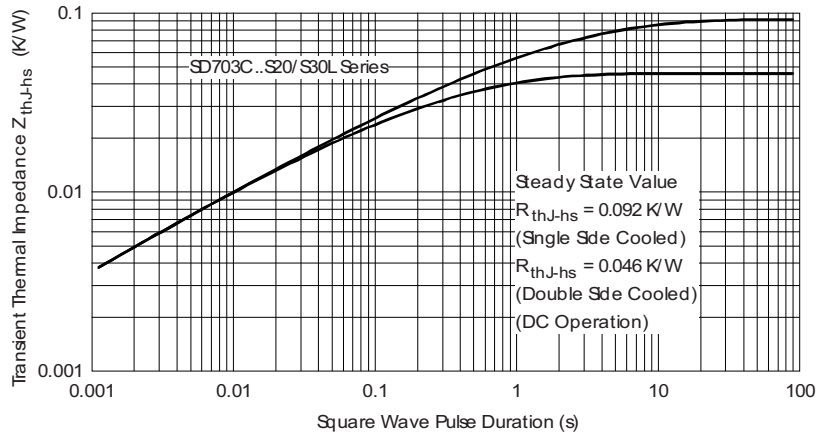


Fig. 19 - Thermal Impedance Z_{thJ-hs} Characteristic

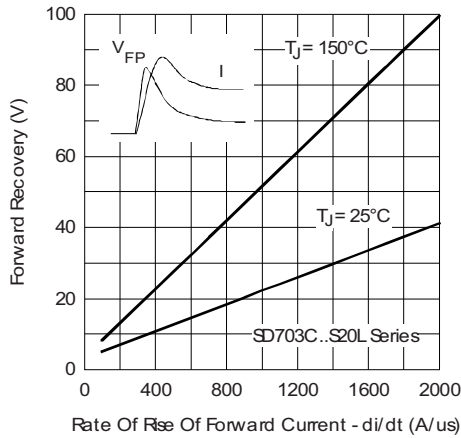


Fig. 20 - Typical Forward Recovery Characteristics

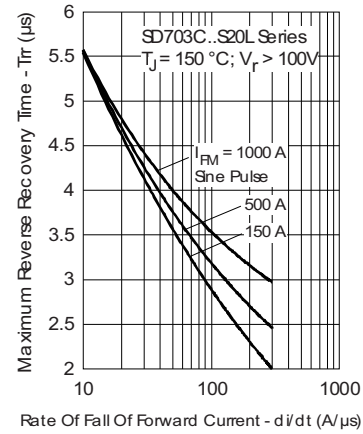


Fig. 22 - Recovery Time Characteristics

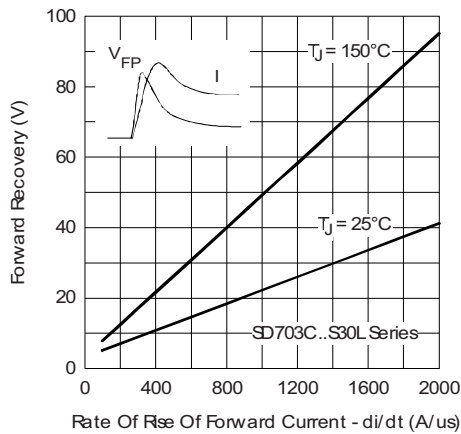


Fig. 21 - Typical Forward Recovery Characteristics

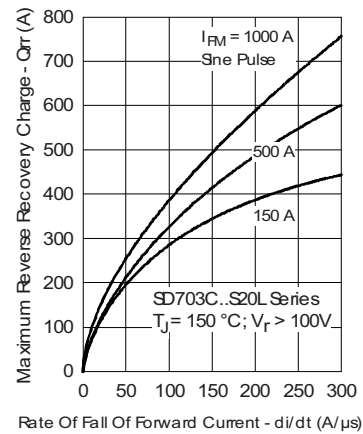


Fig. 23 - Recovery Charge Characteristics

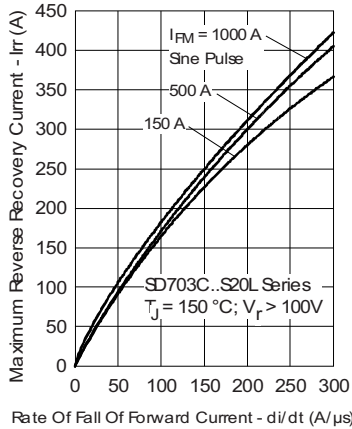


Fig. 24 - Recovery Current Characteristics

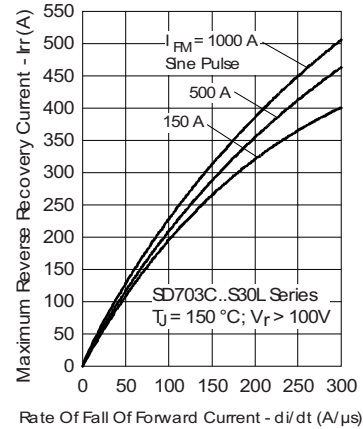


Fig. 27 - Recovery Current Characteristics

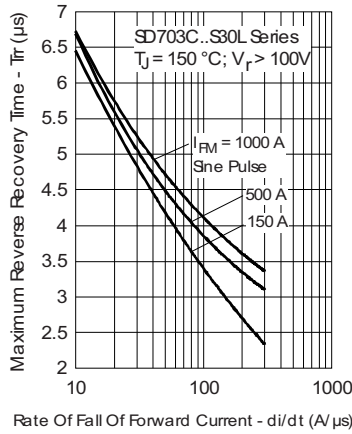


Fig. 25 - Recovery Time Characteristics

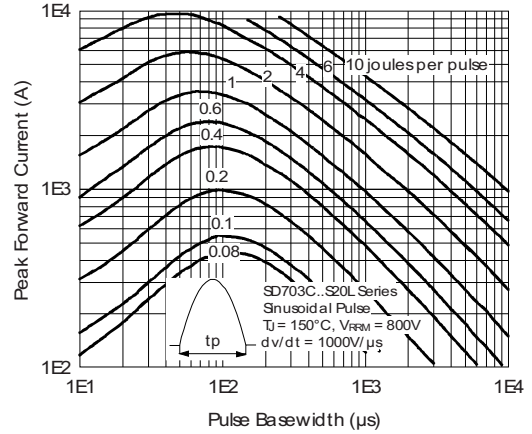


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

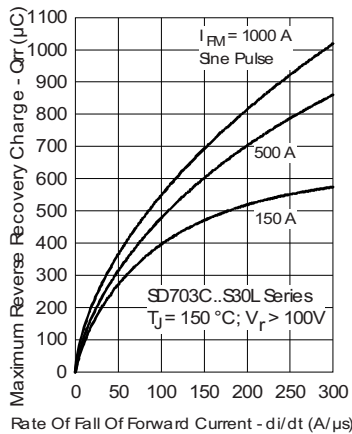


Fig. 26 - Recovery Charge Characteristics

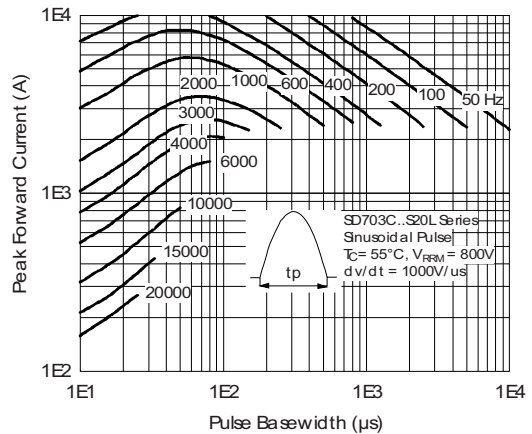


Fig. 29 - Frequency Characteristics

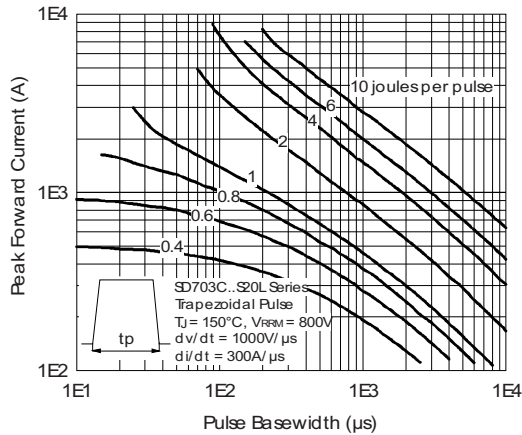


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

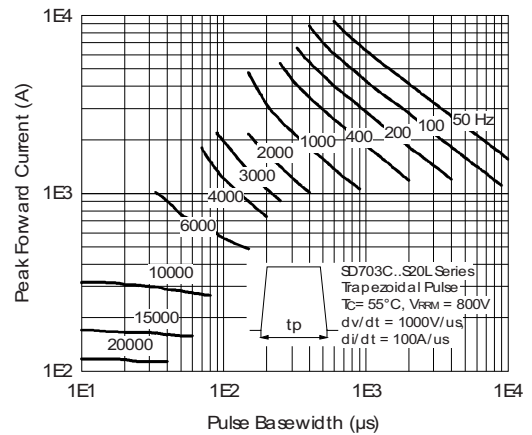


Fig. 33 - Frequency Characteristics

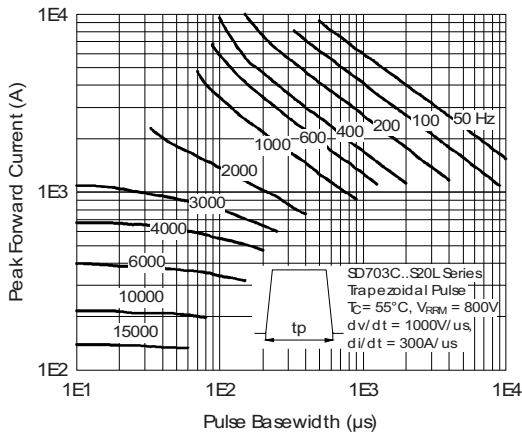


Fig. 31 - Frequency Characteristics

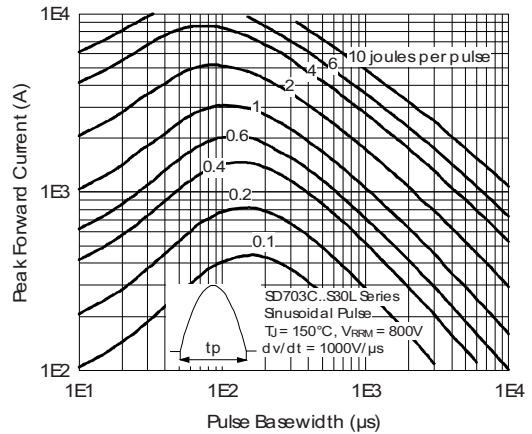


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

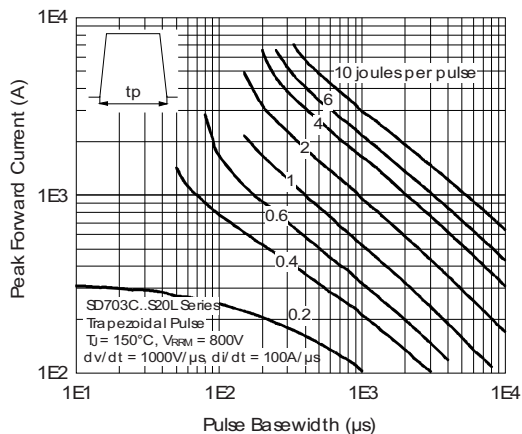


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

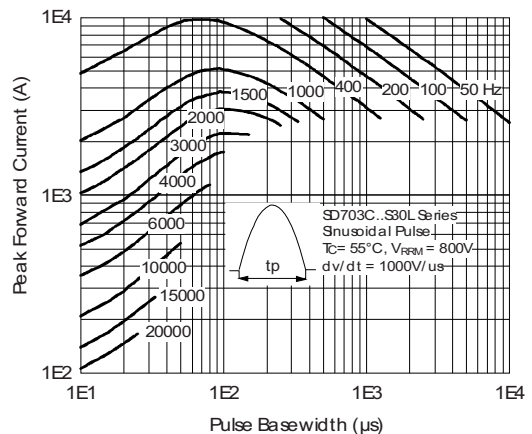


Fig. 35 - Frequency Characteristics

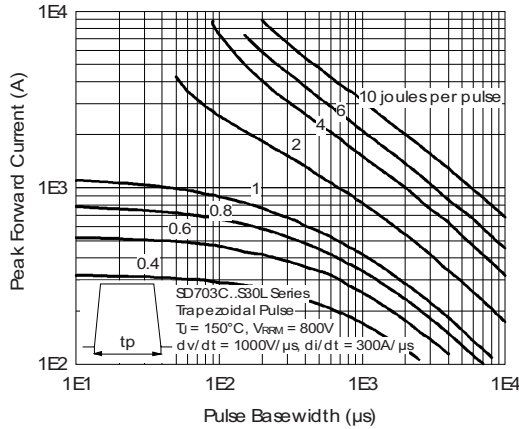


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

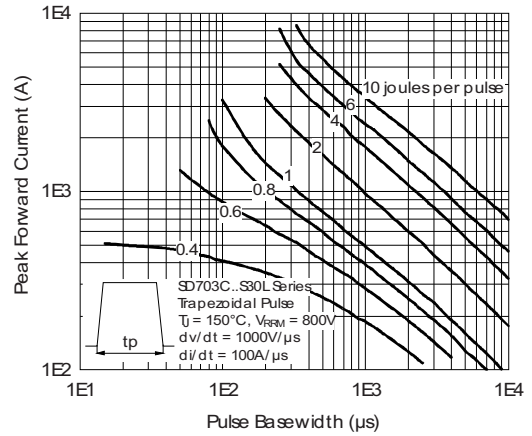


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

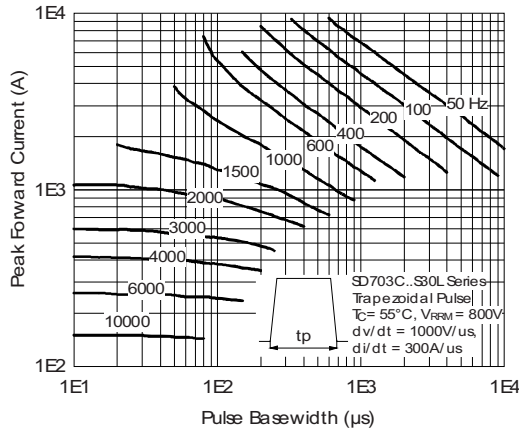


Fig. 37 - Frequency Characteristics

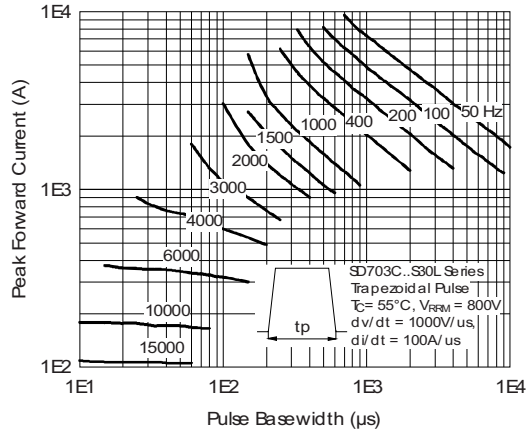


Fig. 39 - Frequency Characteristics

ORDERING INFORMATION TABLE

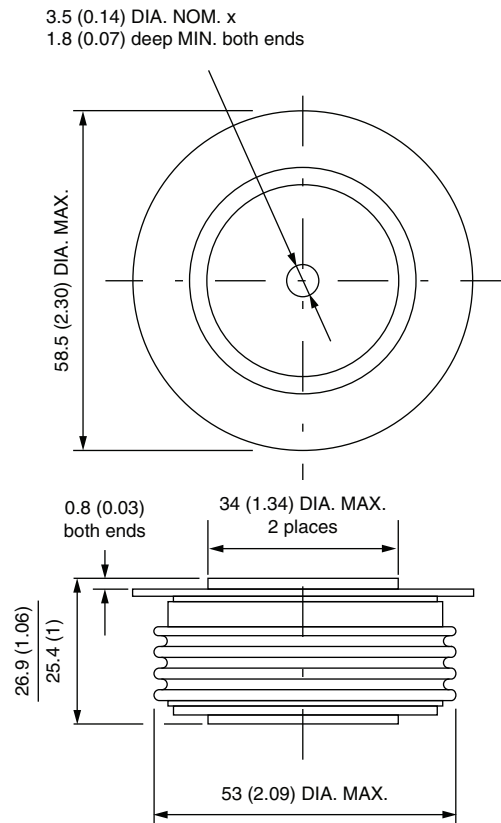
Device code	VS-	SD	70	3	C	25	S20	L
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Vishay Semiconductors product
- 2** - Diode
- 3** - Essential part number
- 4** - 3 = Fast recovery
- 5** - C = Ceramic PUK
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** - t_{rr} code
- 8** - L = PUK case DO-200AB (B-PUK)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95246

DO-200AB (B-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)



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<http://moschip.ru/get-element>

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

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